













SCES323Q - JUNE 2001 - REVISED MARCH 2017

SN74LVC1G66

SN74LVC1G66 Single Bilateral Analog Switch

Features

- Available in the Texas Instruments NanoFree™ Package
- 1.65-V to 5.5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 0.8 ns at 3.3 V
- High On-Off Output Voltage Ratio
- High Degree of Linearity
- High Speed, Typically 0.5 ns ($V_{CC} = 3 \text{ V}$, $C_{L} = 50 \text{ pF}$
- Low ON-State Resistance, Typically ≉5.5 Ω (V_{CC}
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

2 Applications

- Wireless Devices
- Audio and Video Signal Routing
- Portable Computing
- Wearable Devices
- Signal Gating, Chopping, Modulation or Demodulation (Modem)
- Signal Multiplexing for Analog-to-Digital and Digital-to-Analog Conversion Systems

3 Description

This single analog switch is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G66 device can handle analog and digital signals. The device permits bidirectional transmission of signals with amplitudes of up to 5.5 V (peak).

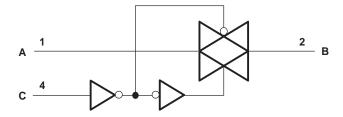
NanoFree package technology major is breakthrough in IC packaging concepts, using the die as the package.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
SN74LVC1G66DBV	SOT-23 (5)	2.90 mm × 1.60 mm		
SN74LVC1G66DCK	SC70 (5)	2.00 mm × 1.25 mm		
SN74LVC1G66DRL	SOT (5)	1.60 mm × 1.20 mm		
SN74LVC1G66DRY	SON (6)	1.45 mm × 1.00 mm		
SN74LVC1G66YZP	DSBGA (5)	1.39 mm × 0.89 mm		
SN74LVC1G66DSF	SON (6)	1.00 mm x 1.00 mm		

(1) For all available packages, see the orderable addendum at the end of the datasheet.

Logic Diagram (Positive Logic)



Features 1

Applications 1



8.2 Functional Block Diagram 13

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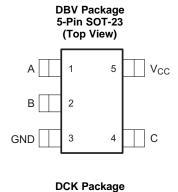
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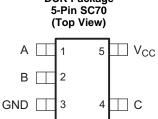
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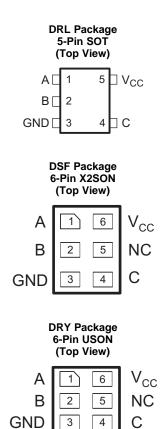
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5 Pin Configuration and Functions



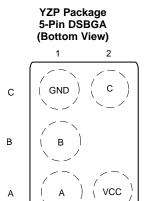




Pin Functions

	PIN						
NAME	SOT NO.	USON, X2SON NO.	I/O	DESCRIPTION			
Α	1	1	I/O	I/O Bidirectional signal to be switched			
В	2	2	I/O	Bidirectional signal to be switched			
С	4	4	I	Controls the switch (L = OFF, H = ON)			
GND	3	3	_	Ground pin			
NC	_	5	_	Do not connect			
V _{CC}	5	6	_	Power pin			





Pin Functions

	PIN			
NAME	DSBGA NO.	I/O	DESCRIPTION	
Α	A1	I/O	Bidirectional signal to be switched	
В	B1	I/O	Bidirectional signal to be switched	
С	C2	I	Controls the switch (L = OFF, H = ON)	
GND	C1	_	Ground pin	
V _{CC}	A2	_	Power pin	



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V_{CC}	Supply voltage ⁽²⁾		-0.5	6.5	V
V_{I}	· · · · · · · · · · · · · · · · · · ·			6.5	V
V _{I/O}	Switch I/O voltage ⁽²⁾⁽³⁾⁽⁴⁾	-0.5	V _{CC} + 0.5	V	
I_{IK}	Control input clamp current	V _I < 0		-50	mA
I _{IOK}	I/O port diode current	$V_{I/O}$ < 0 or $V_{I/O}$ > V_{CC}		±50	mA
I _T	ON-state switch current	$V_{I/O}$ < 0 to V_{CC}		±50	mA
	Continuous current through V _{CC} or GND		±100	mA	
T _{stg}	T _{stg} Storage Temperature			150	°C
Tj	Junction Temperature			150	°C

⁽¹⁾ Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	+2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	+1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT	
V _{CC}	Supply voltage		1.65	5.5	V	
V _{I/O}	I/O port voltage.		0	V _{CC}	V	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	$V_{CC} \times 0.65$			
\/	High level input voltage, control input	V _{CC} = 2.3 V to 2.7 V	V _{CC} × 0.7		V	
V_{IH}	High-level input voltage, control input	V _{CC} = 3 V to 3.6 V	V _{CC} × 0.7			
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$V_{CC} \times 0.7$			
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$V_{CC} \times 0.35$		
.,	Low-level input voltage, control input	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		$V_{CC} \times 0.3$	V	
V_{IL}		V _{CC} = 3 V to 3.6 V		V _{CC} × 0.3	V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$V_{CC} \times 0.3$		
VI	Control input voltage		0	5.5	V	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		20		
41/4	Operational former transmitters of the second fall these	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		20	A /	
Δt/Δv	Control input transition rise and fall time	V _{CC} = 3 V to 3.6 V		10	ns/V	
		V _{CC} = 4.5 V to 5.5 V		10		
T _A	Operating free-air temperature		-40	85	°C	

All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

⁽²⁾ All voltages are with respect to ground, unless otherwise specified.

⁽³⁾ The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁽⁴⁾ This value is limited to 5.5 V maximum.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.4 Thermal Information

		SN74LVC1G66						
	THERMAL METRIC		DCK (SC70)	DRL (SOT)	DRY (USON)	DSF (X2SON)	YZP (DSBGA)	UNIT
		5 PINS	5 PINS	5 PINS	6 PINS	6 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	206	252	142		_	132	°C/W

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITI	ONS	V _{CC}	MIN TYP(1)	MAX	UNIT
		$V_{I} = V_{CC}$ or GND,	I _S = 4 mA	1.65 V	12	30	
_	ON state switch resistance	$V_{I} = V_{CC}$ of GND, $V_{C} = V_{IH}$	I _S = 8 mA	2.3 V	9	20	Ω
r _{on}	ON-state switch resistance	(see Figure 2 and	I _S = 24 mA	3 V	7.5	15	12
		Figure 1)	I _S = 32 mA	4.5 V	5.5	10	
		V. – V or GND	$I_S = 4 \text{ mA}$	1.65 V	74.5	120	
_	Peak on resistance	$V_I = V_{CC}$ or GND, $V_C = V_{IH}$	$I_S = 8 \text{ mA}$	2.3 V	20	30	Ω
r _{on(p)}	reak on resistance	(see Figure 2 and	I _S = 24 mA	3 V	11.5	20	12
		Figure 1)	I _S = 32 mA	4.5 V	7.5	15	
		$V_I = V_{CC}$ and $V_O = GND$ or				±1	
I _{S(off)}	OFF-state switch leakage current	$V_I = GND$ and $V_O = V_{CC}$, $V_C = V_{IL}$ (see Figure 3)	T _A = 25°C	5.5 V		±0.1	μА
		$V_I = V_{CC}$ or GND, $V_C = V_{IH}$,				±1	
I _{S(on)}	ON-state switch leakage current	V _O = Open (see Figure 4)	T _A = 25°C	5.5 V		±0.1	μА
I.	Control input current	$V_C = V_{CC}$ or GND		5.5 V		±1	^
l _l	Control input current	AC = ACC OL GIAD	T _A = 25°C	3.5 V		±0.1	μΑ
1	Supply current	$V_C = V_{CC}$ or GND		5.5 V		10	
I _{CC}	Supply current	AC = ACC OL GIAD	T _A = 25°C	3.5 V		1	μА
ΔI_{CC}	Supply current change	$V_C = V_{CC} - 0.6 V$		5.5 V		500	μΑ
C _{ic}	Control input capacitance			5 V	2		pF
C _{io(off)}	Switch input and output capacitance			5 V	6		pF
C _{io(on)}	Switch input and output capacitance			5 V	13		рF

⁽¹⁾ $T_A = 25^{\circ}C$

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 5)

	PARAMETER	FROM	TO (OUTBUT)	V _{CC} = ± 0.1		V _{CC} = 2.5 V ± 0.2 V																												V _{CC} = 5 V ± 0.5 V		UNIT
. , , , , , , , , , , , , , , , , , , ,	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX																										
	t _{pd} ⁽¹⁾	A or B	B or A		2		1.2		0.8		0.6	ns																								
	t _{en} ⁽²⁾	С	A or B	2.5	12	1.9	6.5	1.8	5	1.5	4.2	ns																								
	t _{dis} (3)	С	A or B	2.2	10	1.4	6.9	2	6.5	1.4	5	ns																								

⁽¹⁾ t_{PLH} and t_{PHL} are the same as t_{pd}. The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

 ⁽²⁾ t_{PZL} and t_{PZH} are the same as t_{en}.
 (3) t_{PLZ} and t_{PHZ} are the same as t_{dis}.



6.7 Analog Switch Characteristics

 $T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _{cc}	TYP	UNIT
				1.65 V	35	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	120	1
	A or B		(see Figure 6)	3 V	175	ı
Frequency response ⁽¹⁾		D A	,	4.5 V	195	
(switch ON)	A OF B	B Of A		1.65 V	>300	IVIHZ
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	>300	Ì
		$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				
			,	4.5 V	.5 V >300 65 V 35 .3 V 50	ı
				1.65 V	35	i
Crosstalk	0	A or B	or B $f_{in} = 1$ MHz (square wave) (see Figure 7) 3 V 70	\/		
(control input to signal output)	С			3 V	70	m۷
				1.65 V	-58	i
			f _{in} = 1 MHz (sine wave)	2.3 V	-58	dB
				3 V	-58	
Feedthrough attenuation (2)	A == D	D == 4		4.5 V	-58	
(switch OFF)	A or B	B Of A		1.65 V	-42	
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	-42	ı
			(see Figure 8)	3 V	-42	ı
			31 1 1	4.5 V	-42	ı
				1.65 V	0.1%	i
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	2.3 V	0.025%	Ī
			f _{in} = 1 kHz (sine wave) (see Figure 9)	3 V	0.015%	ĺ
Cin a viva in diatantia in	A == D	D == 4	,	4.5 V	0.01%	İ
Sine-wave distortion	A or B	B or A		1.65 V	0.15%	İ
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	2.3 V	0.025%	İ
			f _{in} = 10 kHz (sine wave) (see Figure 9)	3 V	0.015%	<u> </u>
				4.5 V	0.01%	Ī

⁽¹⁾ Adjust f_{in} voltage to obtain 0 dBm at output. Increase f_{in} frequency until dB meter reads -3 dB. (2) Adjust f_{in} voltage to obtain 0 dBm at input.

6.8 Operating Characteristics

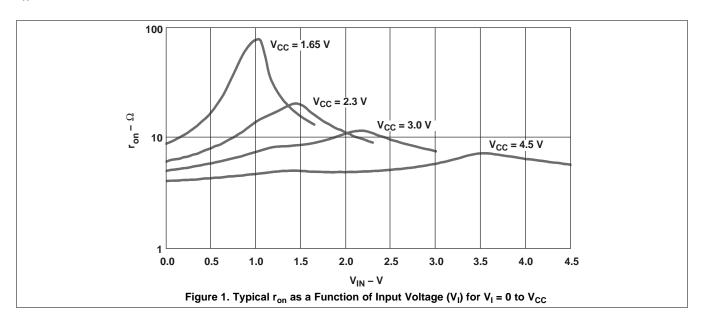
 $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V TYP	V _{CC} = 2.5 V TYP	V _{CC} = 3.3 V TYP	V _{CC} = 5 V TYP	UNIT
C_{pd}	Power dissipation capacitance	f = 10 MHz	8	9	9	11	pF



6.9 Typical Characteristics

 $T_A = 25^{\circ}C$





7 Parameter Measurement Information

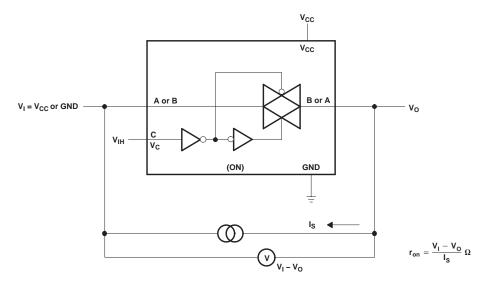


Figure 2. ON-State Resistance Test Circuit

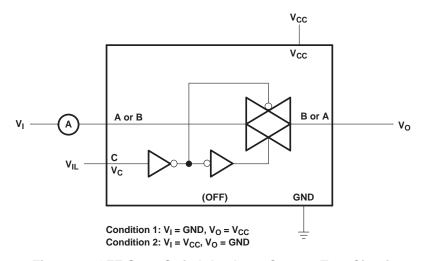


Figure 3. OFF-State Switch Leakage-Current Test Circuit

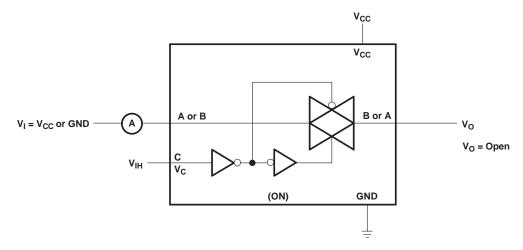
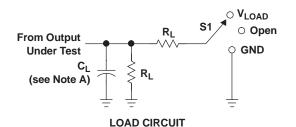


Figure 4. ON-State Switch Leakage-Current Test Circuit

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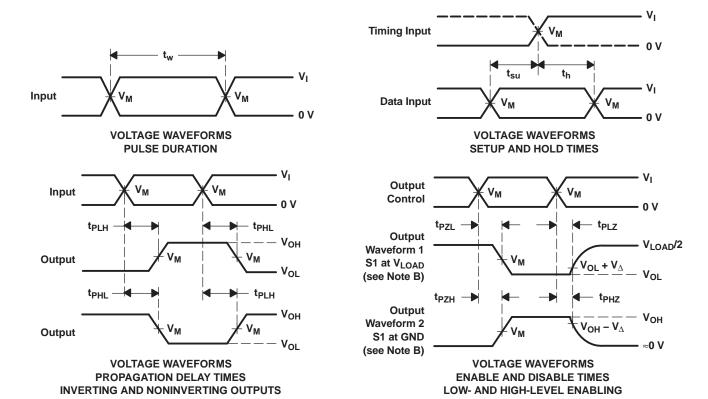


Parameter Measurement Information (continued)



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

	INI	PUTS	.,	V	0		.,
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	R _L	$V_{\!\scriptscriptstyle \Delta}$
1.8 V ± 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	v_{cc}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	V_{CC}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	V_{CC}	≤2.5 ns	V _{CC} /2	2×V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en}.
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 5. Load Circuit and Voltage Waveforms

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Parameter Measurement Information (continued)

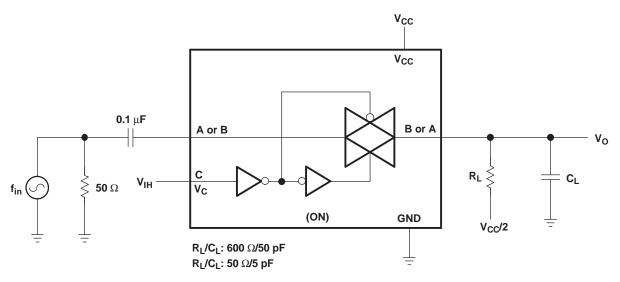


Figure 6. Frequency Response (Switch ON)

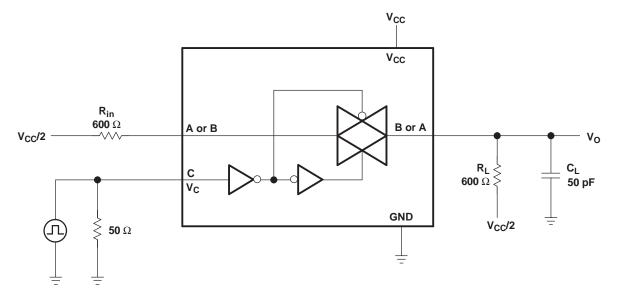


Figure 7. Crosstalk (Control Input – Switch Output)



Parameter Measurement Information (continued)

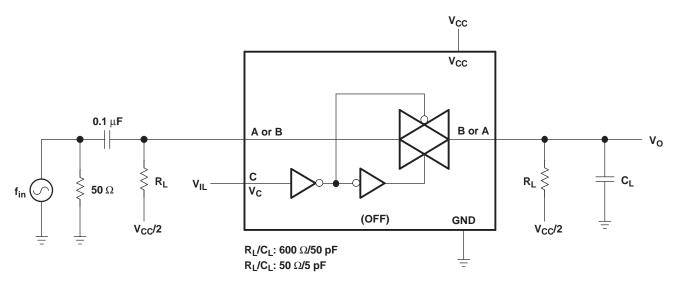


Figure 8. Feedthrough (Switch OFF)

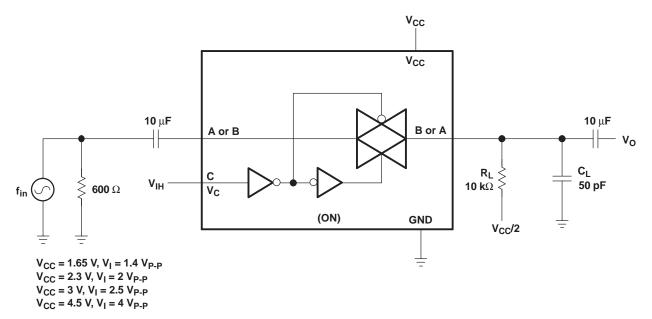


Figure 9. Sine-Wave Distortion

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8 Detailed Description

8.1 Overview

This single analog switch is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G66 device can handle analog and digital signals. The device permits bidirectional transmission of signals with amplitudes of up to 5.5 V (peak). Like all analog switches, the SN74LVC1G66 is bidirectional.

NanoFree package technology is a major breakthrough in IC packaging concepts, using the die as the package.

8.2 Functional Block Diagram

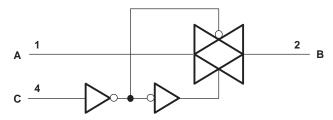


Figure 10. Logic Diagram (Positive Logic)

8.3 Feature Description

The TI NanoFree package is one of TI's smallest packages and allows customers to save board space while the solder bumps allow for easy testing. The SN74LVC1G66 has a wide V_{CC} range, allowing rail-to-rail operation of signals anywhere from a 1.8-V system to a 5-V system. In addition, the control input (C Pin) is 5.5-V tolerant, allowing higher-voltage logic to interface to the switch control system.

8.4 Device Functional Modes

Table 1. Function Table

CONTROL INPUT (C)	SWITCH
L	OFF
Н	ON



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC1G66 can be used in any situation where an SPST switch would be used and a solid-state, voltage-controlled version is preferred.

9.2 Typical Application

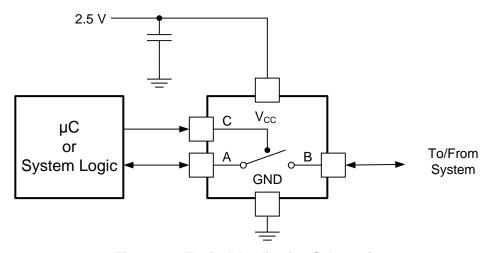


Figure 11. Typical Application Schematic

9.2.1 Design Requirements

The SN74LVC1G66 allows on and off control of analog and digital signals with a digital control signal. All input signals should remain between 0 V and V_{CC} for optimal operation.

9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
 - For rise time and fall time specifications, see Δt/Δv in Recommended Operating Conditions.
 - For specified high and low levels, see V_{IH} and V_{IL} in Recommended Operating Conditions.
 - Inputs and outputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}.
- 2. Recommended Output Conditions:
 - Load currents should not exceed ±50 mA.
- 3. Frequency Selection Criterion:
 - Maximum frequency tested is 150 MHz.
 - Added trace resistance/capacitance can reduce maximum frequency capability; use layout practices as directed in Layout.

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Typical Application (continued)

9.2.3 Application Curve

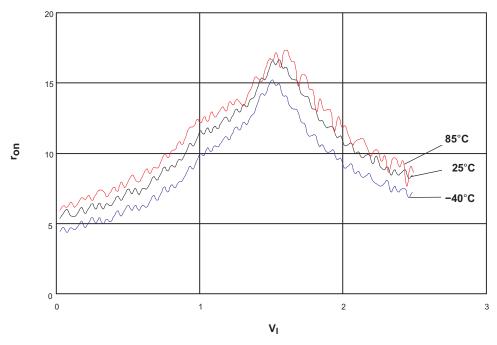


Figure 12. r_{on} vs V_l , $V_{CC} = 2.5 \text{ V (SN74LVC1G66)}$

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μF bypass capacitor is recommended. If there are multiple pins labeled V_{CC} , then a 0.01- μF or 0.022- μF capacitor is recommended for each V_{CC} because the V_{CC} pins will be tied together internally. For devices with dual supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μF bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μF and 1- μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to loop antenna theory, but different enough to warrant their own discussion. When a PCB trace turns a corner at a 90° angle, a reflection can occur. This is primarily due to the change of width of the trace. At the apex of the turn, the trace width is increased to 1.414 times its width. This upsets the transmission line characteristics, especially the distributed capacitance and self–inductance of the trace — resulting in the reflection. It is a given that not all PCB traces can be straight, and so they will have to turn corners. Figure 13 shows progressively better techniques of rounding corners. Only the last example maintains constant trace width and minimizes reflections.



11.2 Layout Example

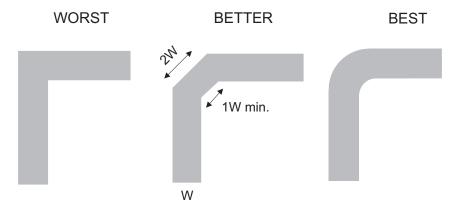


Figure 13. Trace Example

Submit Documentation Feedback

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12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

• Implications of Slow or Floating CMOS Inputs, SCBA004

12.2 Trademarks

NanoFree is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G66DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(C665, C66J, C66R, C66T)	Samples
SN74LVC1G66DBVT	OBSOLETE	SOT-23	DBV	5		TBD	Call TI	Call TI	-40 to 85	(C665, C66J, C66R)	
SN74LVC1G66DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(C65, C6F, C6J, C6 K, C6O, C6R, C 6T)	Samples
SN74LVC1G66DCKT	OBSOLETE	SC70	DCK	5		TBD	Call TI	Call TI	-40 to 85	(C65, C6J, C6R, C6 T)	
SN74LVC1G66DRLR	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(C67, C6R)	Samples
SN74LVC1G66DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C6	Samples
SN74LVC1G66DSF2	OBSOLETE	SON	DSF	6		TBD	Call TI	Call TI	-40 to 85	C6	
SN74LVC1G66DSFR	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C6	Samples
SN74LVC1G66YZPR	ACTIVE	DSBGA	YZP	5	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C6N	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: Til defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

PACKAGE OPTION ADDENDUM

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(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74LVC1G66:

Automotive: SN74LVC1G66-Q1

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G66DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LVC1G66DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G66DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74LVC1G66DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G66DSFR	SON	DSF	6	5000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC1G66YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G66DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G66DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G66DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0
SN74LVC1G66DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G66DSFR	SON	DSF	6	5000	210.0	185.0	35.0
SN74LVC1G66YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0





NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.









NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.





NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).





NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.





NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



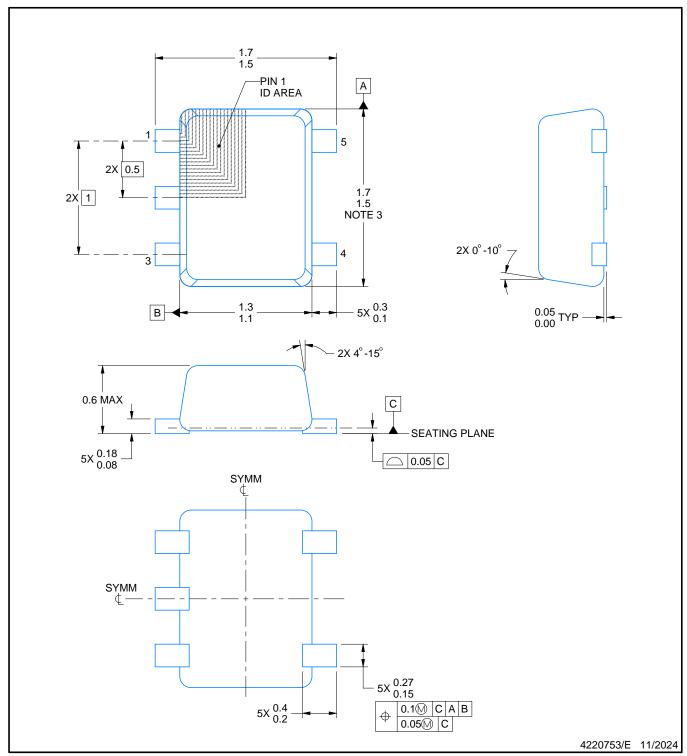


4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





PLASTIC SMALL OUTLINE

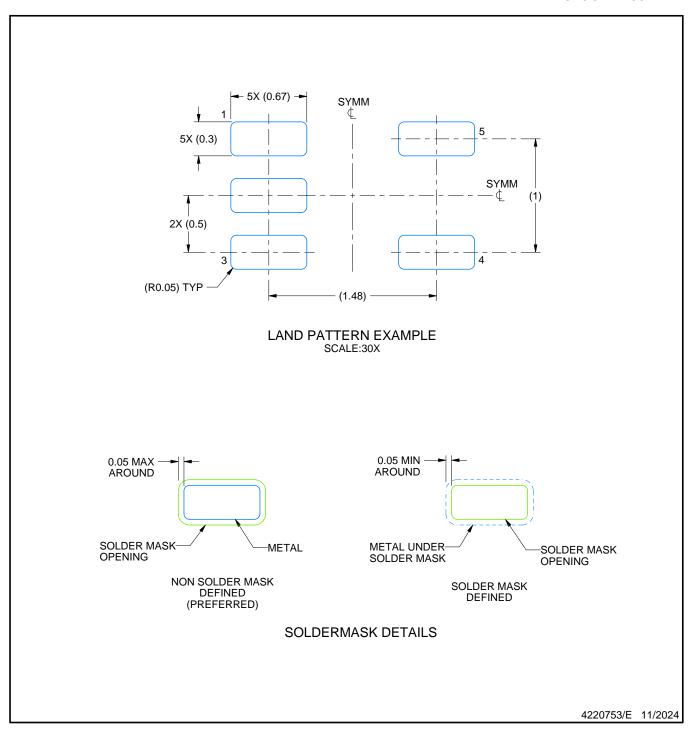


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD-1



PLASTIC SMALL OUTLINE

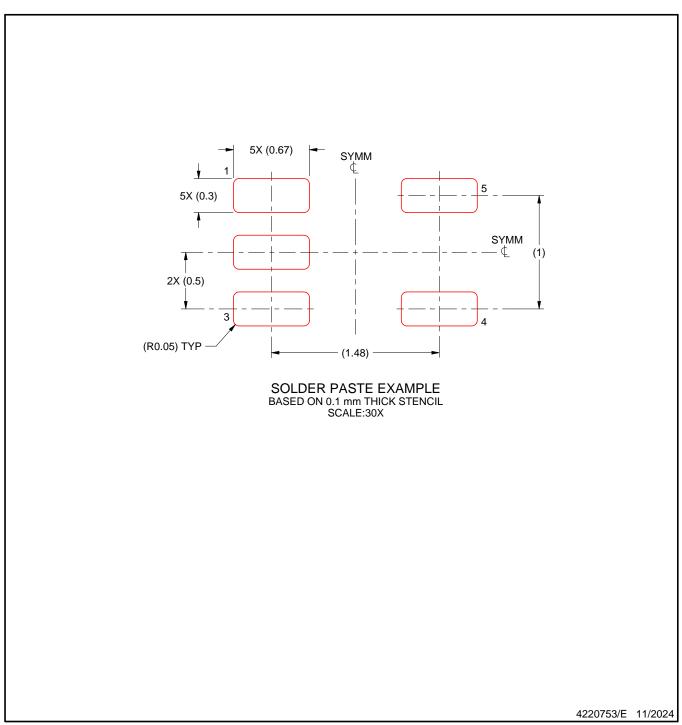


NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side





NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.





DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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